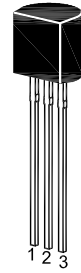


2SA1266

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.
The transistor is subdivided into three groups, O,
Y and G according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 2\text{ mA}$ at $-V_{CE} = 6\text{ V}$, $-I_C = 150\text{ mA}$ Current Gain Group O Y G	h_{FE}	70	140	-
	h_{FE}	120	240	-
	h_{FE}	200	400	-
	h_{FE}	25	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{BE(sat)}$	-	1.1	V
Transition Frequency at $-V_{CE} = 10\text{ V}$, $-I_C = 1\text{ mA}$	f_T	80	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	7	pF

